

# SKN 2F17



Stud Diode

## Fast Recovery Rectifier Diode

SKN 2F17

SKR 2F17

### Features

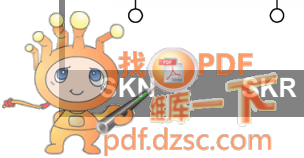
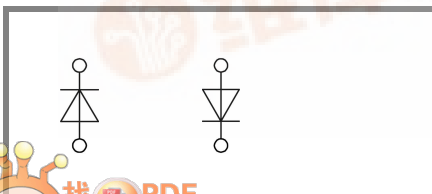
- Small recovered charge
- Soft recovery
- Up to 1000 V reverse voltage
- Hermetic metal case with glass insulator
- Threaded stud ISO M5 or 10-32 UNF
- SKN: anode to stud
- SKR: cathode to stud

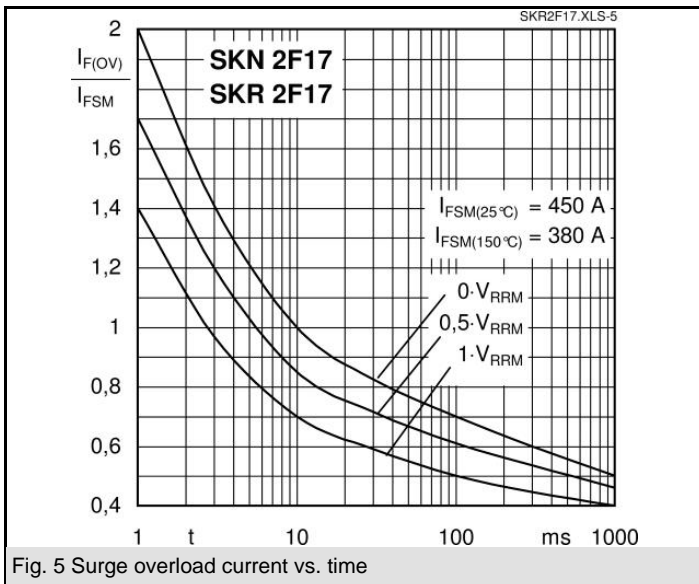
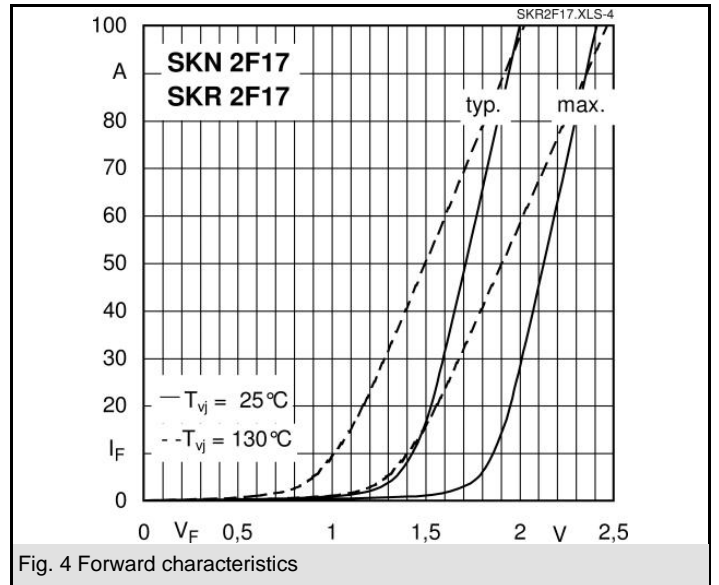
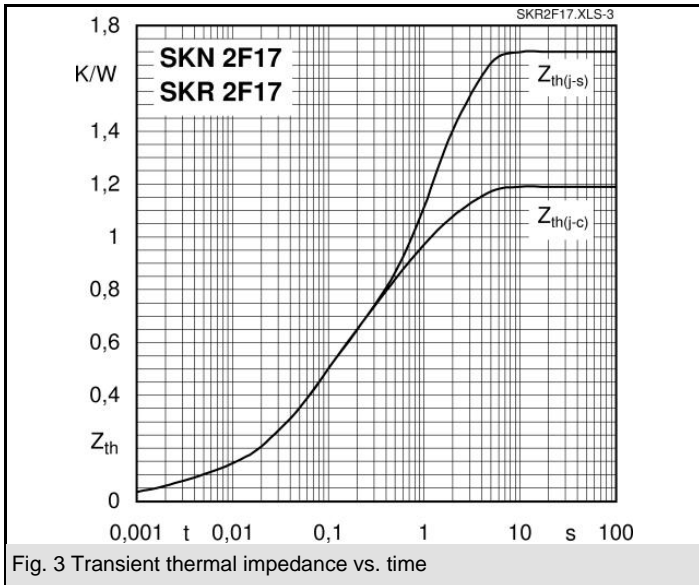
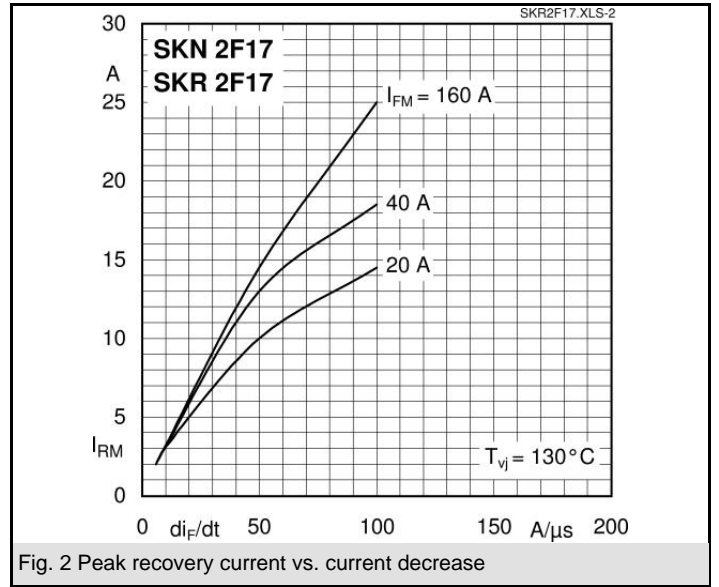
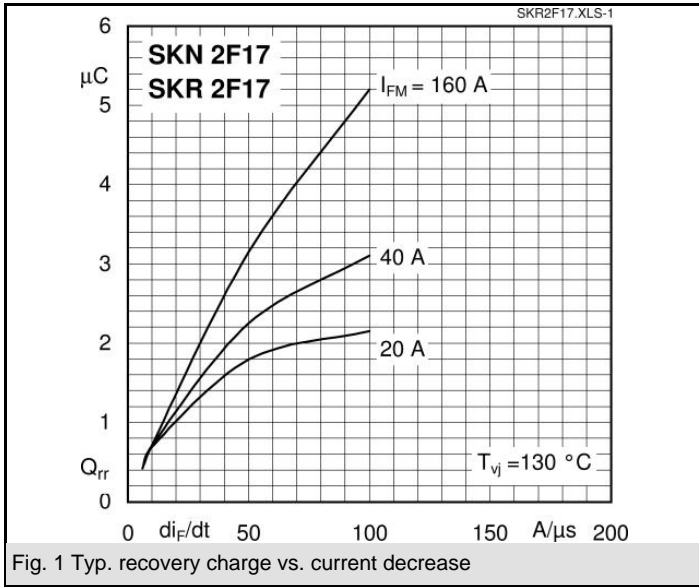
### Typical Applications

- Inverse diode for power transistor, GTO thyristor, asymmetric thyristor
- SMPS, inverters, choppers
- for severe ambient conditions

V <sub>RSM</sub> V	V <sub>RRM</sub> V	I <sub>FRMS</sub> = 41 A (maximum value for continuous operation)	
		I <sub>FAV</sub> = 17 A (sin. 180; 5000Hz; T <sub>c</sub> = 113 °C)	
400	400	SKN 2F17/04	SKR 2F17/04
400	400	SKN 2F17/04UNF	SKR 2F17/04UNF
600	600	SKN 2F17/06	SKR 2F17/06
600	600	SKN 2F17/06UNF	SKR 2F17/06UNF
800	800	SKN 2F17/08	SKR 2F17/08
800	800	SKN 2F17/08UNF	SKR 2F17/08UNF
1000	1000	SKN 2F17/10	SKR 2F17/10
1000	1000	SKN 2F17/10UNF	SKR 2F17/10UNF

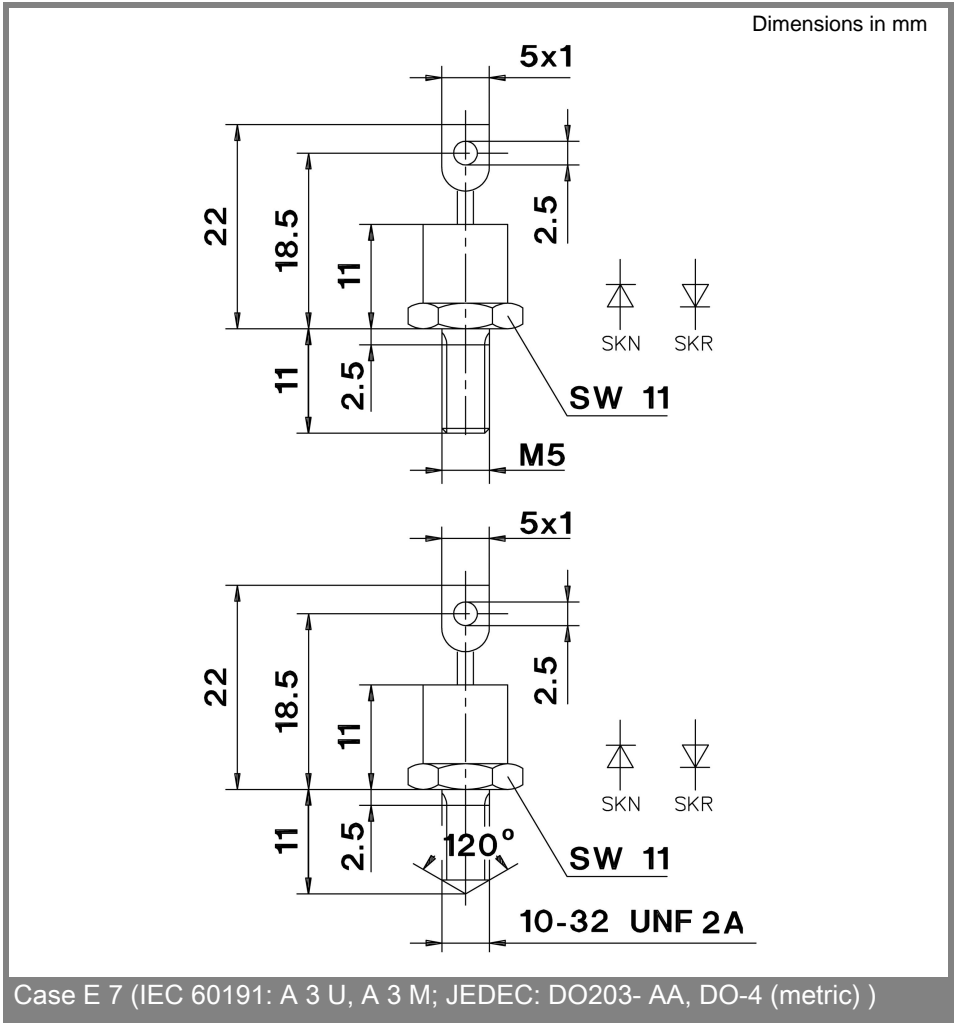
Symbol	Conditions	Values	Units
I <sub>FAV</sub>	sin. 180; T <sub>c</sub> = 85 (100) °C	26 (22)	A
I <sub>FAV</sub>	K5,5; T <sub>a</sub> = 45 °C; sin. 180; 5000 Hz	10	A
I <sub>FSM</sub>	T <sub>vj</sub> = 25 °C; 10 ms	450	A
i <sup>2</sup> t	T <sub>vj</sub> = 150 °C; 10 ms	380	A
	T <sub>vj</sub> = 25 °C; 8,3 ... 10 ms	1000	A <sup>2</sup> s
	T <sub>vj</sub> = 150 °C; 8,3 ... 10 ms	720	A <sup>2</sup> s
V <sub>F</sub>	T <sub>vj</sub> = 25 °C; I <sub>F</sub> = 50 A	max. 2,15	V
V <sub>(TO)</sub>	T <sub>vj</sub> = 130 °C	max. 1,3	V
r <sub>T</sub>	T <sub>vj</sub> = 130 °C	max. 12	mΩ
I <sub>RD</sub>	T <sub>vj</sub> = 25 °C; V <sub>RD</sub> = V <sub>RRM</sub>	max. 0,2	mA
I <sub>RD</sub>	T <sub>vj</sub> = 130 °C; V <sub>RD</sub> = V <sub>RRM</sub>	max. 16	mA
Q <sub>rr</sub>	T <sub>vj</sub> = 130 °C, I <sub>F</sub> = 50 A,	1	μC
I <sub>RM</sub>	-di/dt = 15 A/μs, V <sub>R</sub> = 30 V	4,5	A
t <sub>rr</sub>		440	ns
E <sub>rr</sub>		-	mJ
R <sub>th(j-c)</sub>		1,2	K/W
R <sub>th(c-s)</sub>		0,5	K/W
T <sub>vj</sub>		- 40 ... + 150	°C
T <sub>stg</sub>		- 55 ... + 150	°C
V <sub>isol</sub>		-	V~
M <sub>s</sub>	to heatsink	1,5	Nm
a		5 * 9,81	m/s <sup>2</sup>
m	approx.	7	g
Case		E7	





# SKN 2F17

# TRANSISTOR BRIDGE SCR BRIDGE



Case E 7 (IEC 60191: A 3 U, A 3 M; JEDEC: DO203- AA, DO-4 (metric) )

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